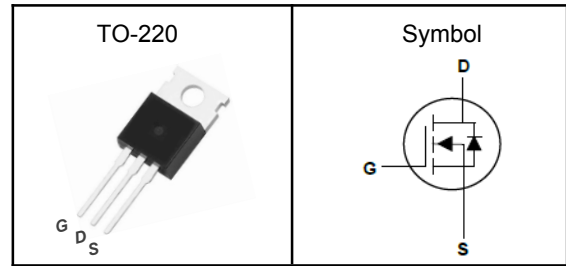


**N-Channel Enhancement Mode MOSFET**
**Features**

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

**Applications**

- Power Management in Desktop Computer
- DC/DC Converters

**Pin Description**


$V_{DSS}$	900	V
$R_{DS(ON)-Typ}$	1700	m $\Omega$
$I_D$	6	A

**Absolute Maximum Ratings**( $T_J=25^\circ\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit	
$V_{DSS}$	Drain-Source Voltage	900	V	
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V	
$T_J$	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$	
$E_{AS}$	Single Pulse Avalanche Energy <sup>③</sup>	180	mJ	
$I_{DM}^{①}$	Pulse Drain Current Tested	24	A	
$I_D$	Continuous Drain Current	$T_c=25^\circ\text{C}$	6	A
$P_D$	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	160	W

**Thermal Characteristics**

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>①</sup>	62.5	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>①</sup>	0.78	$^\circ\text{C/W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150 $^\circ\text{C}$ .

Note ③ : Surface Mounted on 1in<sup>2</sup> FR-4 board with 1oz.



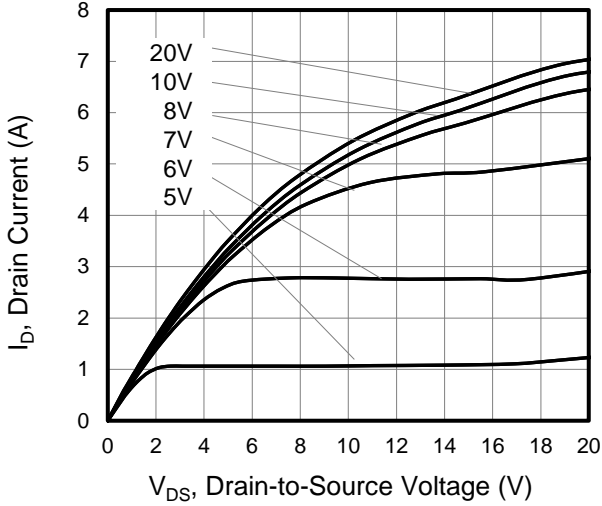
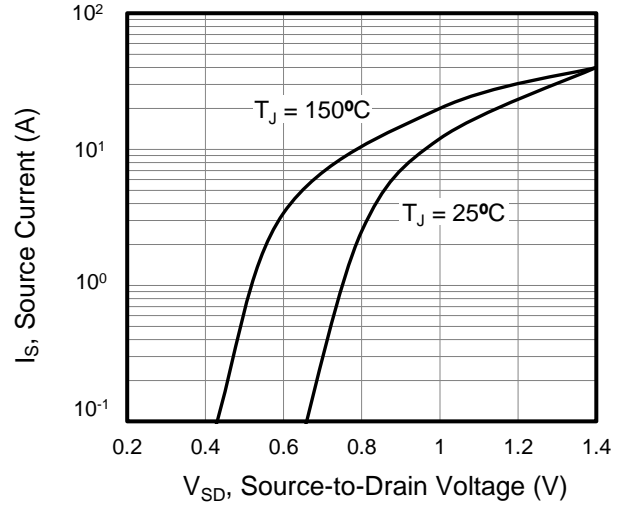
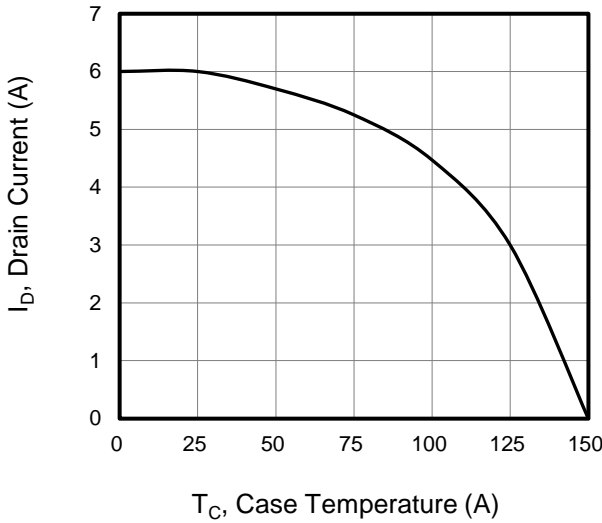
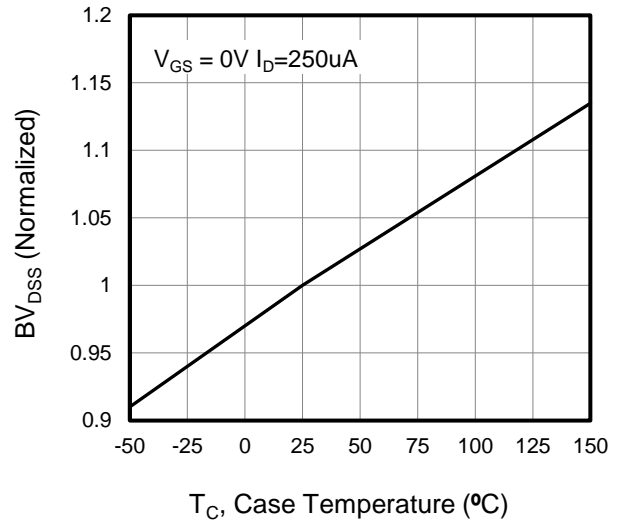
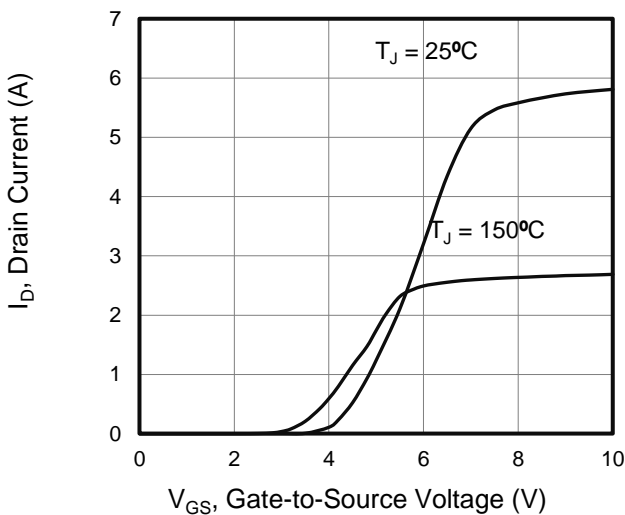
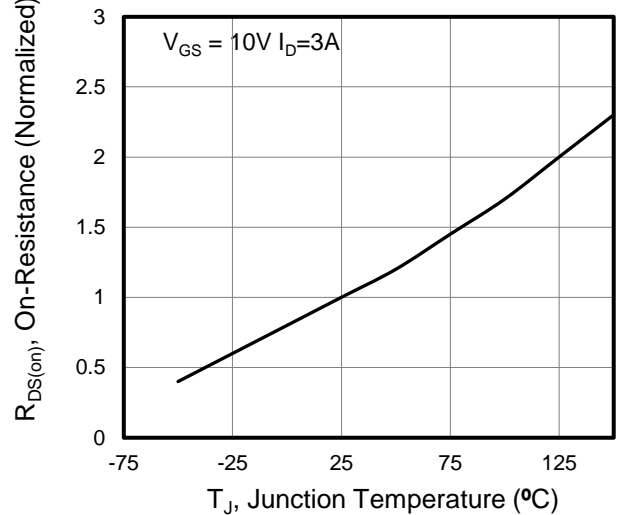
**N-Channel Enhancement Mode MOSFET**

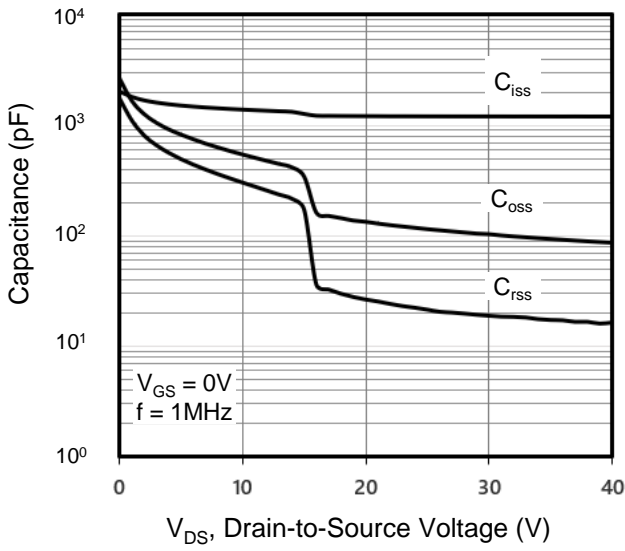
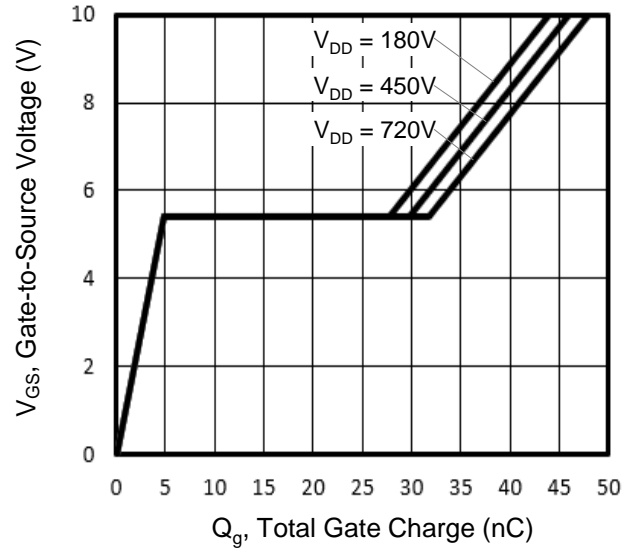
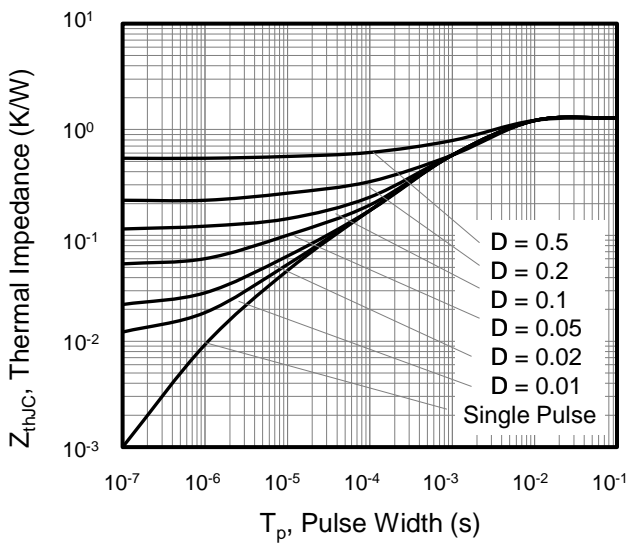
**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$ , Unless Otherwise Noted)

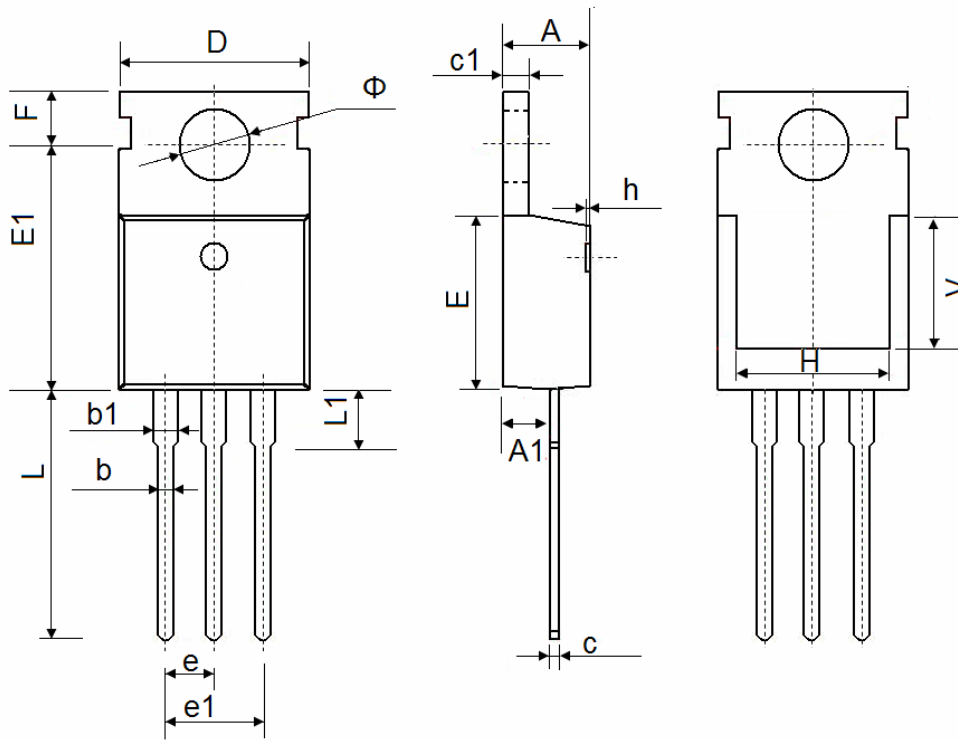
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Static Electrical Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	900	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=900V, V_{GS}=0V$	---	---	1	$\mu A$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	---	4.5	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 30V, V_{DS}=0V$	---	---	$\pm 100$	nA
$R_{DS(ON)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=3A$	---	1700	2000	$m\Omega$
<b>Dynamic Characteristics</b> <sup>⑤</sup>						
$C_{iss}$	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=25V,$ Freq.=1MHz	---	1255	---	pF
$C_{oss}$	Output Capacitance		---	110	---	
$C_{rss}$	Reverse Transfer Capacitance		---	20	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=450V,$ $V_{GS}=10V, R_G=25\Omega,$ $I_D=6A$	---	42	---	nS
$T_r$	Turn-on Rise Time		---	25	---	
$T_{d(off)}$	Turn-off Delay Time		---	203	---	
$T_f$	Turn-off Fall Time		---	42	---	
$Q_g$	Total Gate Charge	$V_{DD}=720V,$ $V_{GS}=10V, I_D=6A$	---	47	---	nC
$Q_{gs}$	Gate-Source Charge		---	8	---	
$Q_{gd}$	Gate-Drain Charge		---	24	---	
<b>Source-Drain Characteristics</b> ( $T_J=25^{\circ}\text{C}$ )						
$V_{SD}$	Diode Forward Voltage <sub>2</sub>	$V_{GS}=0V, I_S=3A, T_J=25^{\circ}\text{C}$	---	---	1.4	V
$t_{rr}$	Reverse Recovery Time	$I_F=6A,$ $di/dt=100A/\mu s, T_J=25^{\circ}\text{C}$	---	520	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	1.5	---	nC

Note ④ : Pulse test (pulse width $\leq 300\mu s$ , duty cycle $\leq 2\%$ ).

Note ⑤ : Guaranteed by design, not subject to production testing.

**N-Channel Enhancement Mode MOSFET**
**Typical Characteristics**
**Figure 1. Output Characteristics ( $T_J = 25^\circ\text{C}$ )**

**Figure 2. Body Diode Forward Voltage**

**Figure 3. Drain Current vs. Temperature**

**Figure 4.  $BV_{DSS}$  Variation vs. Temperature**

**Figure 5. Transfer Characteristics**

**Figure 6. On-Resistance vs. Temperature**


**N-Channel Enhancement Mode MOSFET**
**Figure 7. Capacitance**

**Figure 8. Gate Charge**

**Figure 9. Transient Thermal Impedance**


**N-Channel Enhancement Mode MOSFET**
**TO-220 Package Outline Data**


Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.350	4.650
A1	2.250	2.550
b	0.710	0.910
b1	1.170	1.400
c	0.330	0.650
c1	1.200	1.400
D	9.910	10.250
E	8.9500	9.750
E1	12.650	12.950
e	2.540 TYP.	
e1	4.980	5.180
F	2.650	2.950
H	7.900	8.100
h	0.000	0.300
L	12.700	13.500
L1	2.850	3.250
V	7.500 REF.	
Φ	3.400	3.800